



## **Improved Quad CMOS Analog Switches**

#### **DESCRIPTION**

The DG308B, DG309B analog switches are highly improved versions of the industry-standard DG308A, DG309. These devices are fabricated in Vishay Siliconix' proprietary silicon gate CMOS process, resulting in lower on-resistance, lower leakage, higher speed, and lower power consumption.

These quad single-pole single-throw switches are designed for a wide variety of applications in telecommunications, instrumentation, process control, computer peripherals, etc.

An improved charge injection compensation design minimizes switching transients. The DG308B and DG309B can handle up to  $\pm$  22 V input signals. An epitaxial layer prevents latchup.

All devices feature true bi-directional performance in the on condition, and will block signals to the supply levels in the off condition.

The DG308B is a normally open switch and the DG309B is a normally closed switch. (see Truth Table.)

#### **FEATURES**

- ± 22 V supply voltage rating
- CMOS compatible logic
- Low on-resistance  $R_{DS(on)}$ : 45  $\Omega$
- Low leakage I<sub>D(on)</sub>: 20 pA
- Single supply operation possible
- Extended temperature range
- Fast switching t<sub>ON</sub>: < 200 ns</li>
- Low glitching Q: 1 pC

#### **BENEFITS**

- Wide analog signal range
- · Simple logic interface
- Higher accuracy
- · Minimum transients
- Reduced power consumption
- Superior to DG308A, DG309
- Space savings (TSSOP)

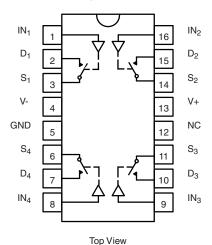
#### **APPLICATIONS**

- · Industrial instrumentation
- Test equipment
- · Communications systems
- Disk drives
- Computer peripherals
- · Portable instruments
- Sample-and-hold circuits

#### **FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION**

#### DG308B

Dual-In-Line, SOIC and TSSOP



TRUTH TABLE						
Logic	DG308B	DG309B				
0	OFF	ON				
1	ON	OFF				

 $\begin{array}{l} \text{Logic "0"} \leq 3.5 \text{ V} \\ \text{Logic "1"} \geq 11 \text{ V} \end{array}$ 

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<sup>\*</sup> Pb containing terminations are not RoHS compliant, exemptions may apply

# DG308B, DG309B

# Vishay Siliconix



ORDERING INFORMATION				
Temp. Range	Package	Part Number		
	16-Pin PlasticDIP	DG308BDJ DG308BDJ-E3		
	10-FIII FIASUCDIF	DG309BDJ DG309BDJ-E3		
	16-Pin Narrow SOIC	DG308BDY DG308BDY-E3 DG308BDY-T1 DG308BDY-T1-E3		
- 40 °C to 85 °C	16-PIII Narrow SOIC	DG309BDY DG309BDY-E3 DG309BDY-T1 DG309BDY-T1-E3		
	46 Pin TOOOD	DG308BDQ DG308BDQ-E3 DG308BDQ-T1 DG308BDQ-T1-E3		
	16-Pin TSSOP	DG309BDQ DG309BDQ-E3 DG309BDQ-T1 DG309BDQ-T1-E3		

ABSOLUTE MAXIMUM RATINGS						
Parameter		Limit	Unit			
Voltages Referenced, V+ to V-		44				
GND		25	1			
Digital Inputs <sup>a</sup> , V <sub>S</sub> , V <sub>D</sub>		(V-) - 2 to (V+) + 2 or 30 mA, whichever occurs first	V			
Current, Any Terminal		30				
Peak Current, S or D (Pulsed at 1 ms, 10 % duty cycle max.)		100	mA mA			
Ctorogo Tomporatura	(AK Suffix)	- 65 to 150	°C			
Storage Temperature	(DJ, DY and DQ Suffix)	- 65 to 125				
Power Dissipation (Package) <sup>b</sup>	16-Pin Plastic DIP <sup>c</sup>	470				
	16-Pin Narrow SOIC and TSSOP <sup>d</sup>	640	mW			
	16-Pin CerDIP <sup>e</sup>	900				

- a. Signals on  $S_X$ ,  $D_X$ , or  $IN_X$  exceeding V+ or V- will be clamped by internal diodes. Limit forward diode current to maximum current ratings. b. All leads welded or soldered to PC board.
- c. Derate 6.5 mW/°C above 75 °C.
- d. Derate 7.6 mW/°C above 75 °C.
- e. Derate 12 mW/°C above 75 °C.



		Test Conditions Unless Specified			A Suffix - 55 °C to 125 °C		<b>D Suffix</b> - 40 °C to 85 °C		
Parameter	Symbol	V+ = 15 V, V- = -15 V $V_{IN} = 11 V, 3.5 V^{f}$	Temp.b	Typ. <sup>c</sup>	Min. <sup>d</sup>	Max. <sup>d</sup>	Min. <sup>d</sup>	Max. <sup>d</sup>	Uni
Analog Switch								•	
Analog Signal Range <sup>e</sup>	V <sub>ANALOG</sub>		Full		- 15	15	- 15	15	٧
Drain-Source On-Resistance	R <sub>DS(on)</sub>	$V_D = \pm 10 \text{ V}, I_S = 1 \text{ mA}$	Room Full	45		85 100		85 100	Ω
R <sub>DS(on)</sub> Match	$\Delta R_{DS(on)}$	5	Room	2					%
Source Off Leakage Current	I <sub>S(off)</sub>	$V_S = \pm 14 \text{ V}, V_D = \pm 14 \text{ V}$	Room Full	± 0.01	- 0.5 - 20	0.5 20	- 0.5 - 5	0.5 5	
Drain Off Leakage Current	I <sub>D(off)</sub>	$V_D = \pm 14 \text{ V}, V_S = \pm 14 \text{ V}$	Room Full	± 0.01	- 0.5 - 20	0.5 20	- 0.5 - 5	0.5 5	nA
Drain On Leakage Current	I <sub>D(on)</sub>	V <sub>S</sub> = V <sub>D</sub> = ± 14 V	Room Full	± 0.02	- 0.5 - 40	0.5 40	- 0.5 - 10	0.5 10	
Digital Control									
Input, Voltage High	$V_{INH}$		Full		11		11		V
Input, Voltage Low	$V_{INL}$		Full			3.5		3.5	1 V
Input Current	I <sub>INH</sub> or I <sub>INL</sub>	V <sub>INH</sub> or V <sub>INL</sub>	Full		- 1	1	- 1	1	μΑ
Input Capacitance	C <sub>IN</sub>		Room	5					рF
Dynamic Characteristics									
Turn-On Time	t <sub>ON</sub>	$V_S = 3 \text{ V}$ , see figure 2	Room			200		200	ns
Turn-Off Time	t <sub>OFF</sub>		Room			150		150	115
Charge Injection	Q	$C_L = 1000 \text{ pF, } V_g = 0 \text{ V, } R_g = 0 \Omega$	Room	1					рC
Source-Off Capacitance	C <sub>S(off)</sub>	$V_S = 0 \text{ V, f} = 1 \text{ MHz,}$	Room	5					
Drain-Off Capacitance	$C_{D(off)}$	V S = 0 V, 1 = 1 WIT12,	Room	5					рF
Channel-On Capacitance	C <sub>D(on)</sub>	$V_D = V_S = 0 \text{ V, f} = 1 \text{ MHz}$	Room	16					
Off-Isolation	OIRR	$C_{\rm L} = 15  \rm pF,  R_{\rm L} = 50  \Omega,$	Room	90					
Channel-to-Channel Crosstalk	X <sub>TALK</sub>	$V_S = 1 V_{RMS}, f = 100 \text{ kHz}$	Room	95					dB
Power Supply									
Positive Supply Current	l+	V <sub>IN</sub> = 0 V or 15 V	Room Full			1 5		1 5	μΑ
Negative Supply Current	l-	VIN - 0 V 01 13 V	Room Full		- 1 - 5		- 1 - 5		μΑ
Power Supply Range for Continuous Operation	V <sub>OP</sub>		Full		± 4	± 22	± 4	± 22	٧

# **DG308B**, **DG309B**

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SPECIFICATIONS <sup>a</sup> (for Single Supply)									
		Test Conditions Unless Specified			<b>A Suffix</b> - 55 °C to 125 °C		<b>D Suffix</b> - 40 °C to 85 °C		
Parameter	Symbol	V+ = 12 V, V- = 0 V $V_{IN} = 11 V, 3.5 V^{f}$	Temp.b	Typ.c	Min.d	Max. <sup>d</sup>	Min. <sup>d</sup>	Max.d	Unit
Analog Switch									
Analog Signal Range <sup>e</sup>	$V_{ANALOG}$		Full		0	12	0	12	V
Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>D</sub> = 3 V, 8 V, I <sub>S</sub> = 1 mA	Room Full	90		160 200		160 200	Ω
Dynamic Characteristics									
Turn-On Time	t <sub>ON</sub>	V 9 V and figure 9	Room			300		300	
Turn-Off Time	t <sub>OFF</sub>	$V_S = 8 V$ , see figure 2	Room			200		200	ns
Charge Injection	Q	$C_L = 1 \text{ nF, } V_{gen} = 6 \text{ V, } R_{gen} = 0 \Omega$	Room	4					рС
Power Supply		· ·							
Positive Supply Current	l+	V 0 V or 10 V	Room Full			1 5		1 5	
Negative Supply Current	I-	$V_{IN} = 0 V \text{ or } 12 V$	Room Full		- 1 - 5		- 1 - 5		μΑ
Power Supply Range for Continuous Operation	V <sub>OP</sub>		Full		4	44	4	44	V

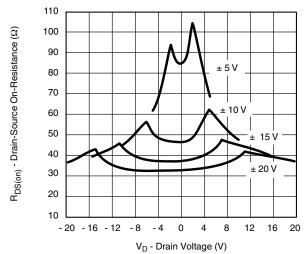
#### Notes:

- a. Refer to PROCESS OPTION FLOWCHART.
- b. Room = 25  $^{\circ}$ C, Full = as determined by the operating temperature suffix.
- c. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.
- d. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
- e. Guaranteed by design, not subject to production test.
- f.  $V_{IN}$  = input voltage to perform proper function.

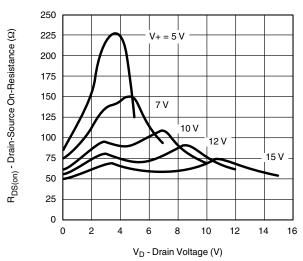
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



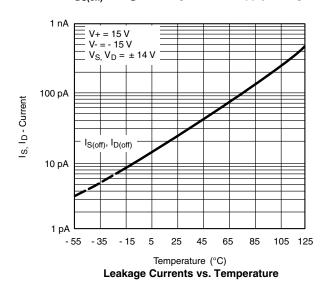
#### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



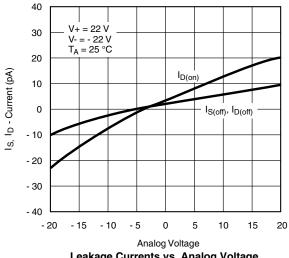
R<sub>DS(on)</sub> vs. V<sub>D</sub> and Power Supply Voltages



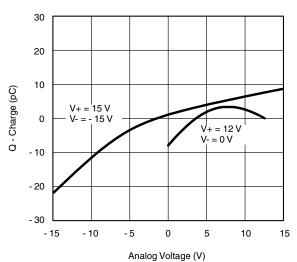
 $R_{DS(on)}$  vs.  $V_D$  and Single Power Supply Voltages



100 V+ = 15 V 90  $\mathsf{R}_{\mathsf{DS}(\mathsf{on})}$  - Drain-Source On-Resistance  $(\Omega)$ 80 70 60 125 50 85<sup>'</sup>°C 40 25 °C 30 - 55<sup>¹</sup>°C 20 10 0 - 15 15 V<sub>D</sub> - Drain Voltage (V)  $\mathbf{R}_{\mathrm{DS(on)}}$  vs.  $\mathbf{V}_{\mathrm{D}}$  and Temperature



Leakage Currents vs. Analog Voltage

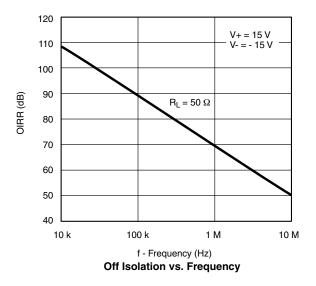


Q<sub>S</sub>, Q<sub>D</sub> - Charge Injection vs. Analog Voltage

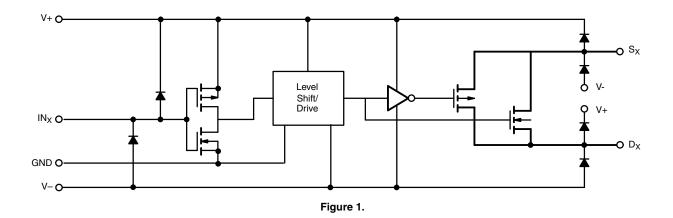
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### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



#### **SCHEMATIC DIAGRAM** (Typical Channel)





#### **TEST CIRCUITS**

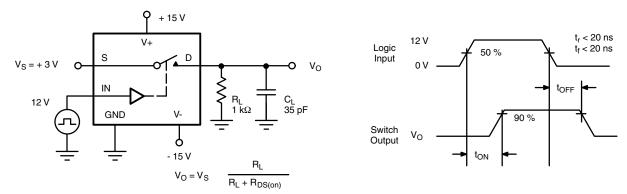


Figure 2. Switching Time

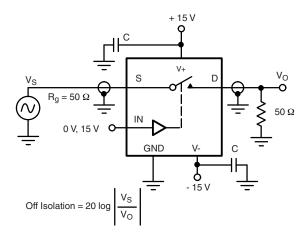


Figure 3. Off Isolation

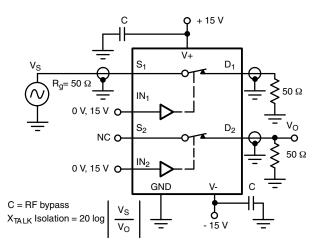
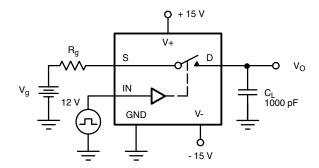
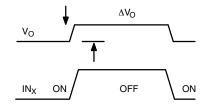


Figure 4. Channel-to-Channel Crosstalk





 $\Delta V_O$  = measured voltage error due to charge injection The charge injection in coulombs is Q = C\_L x  $\Delta V_O$ 

Figure 5. Charge Injection

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#### **APPLICATIONS**

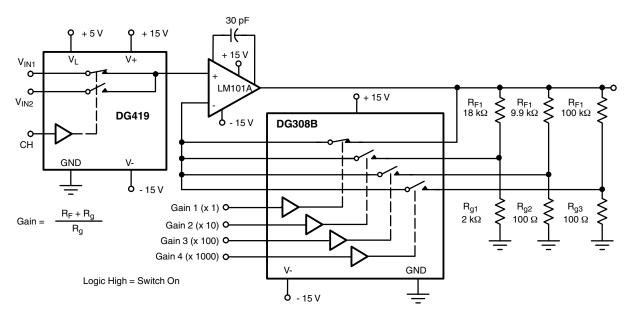


Figure 6. A Precision Amplifier with Digitally Programmable Inputs and Gains

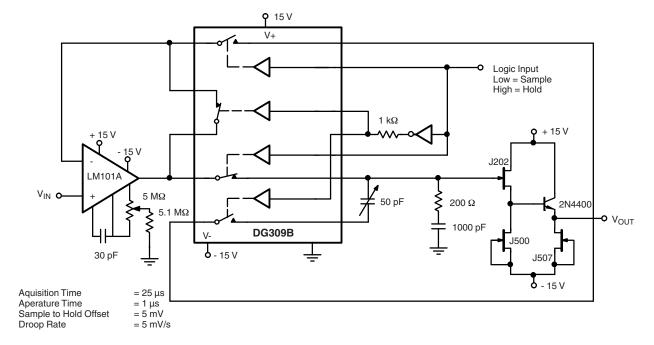
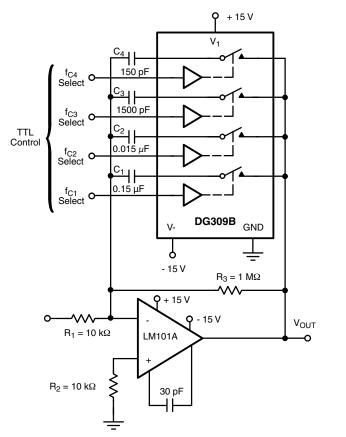
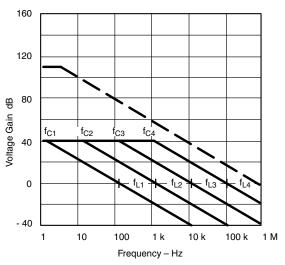


Figure 7. Sample-and-Hold



#### **APPLICATIONS**





$$\begin{array}{ll} A_L \ (\mbox{Voltage Gain Below Break Frequency}) = & \frac{R_3}{R_1} \ = 100 \ (\mbox{40 dB}) \\ f_C \ (\mbox{Break Frequency}) = & \frac{1}{2\pi R_3 C_X} \\ f_L \ (\mbox{Unity Gain Frequency}) = & \frac{1}{2\pi R_1 C_X} \\ \\ \mbox{Max Attenuation} = & \frac{R_{DS(on)}}{10 \ \mbox{k}\Omega} \ \approx -40 \ \mbox{dB} \end{array}$$

Figure 8. Active Low Pass Filter with Digitally Selected Break Frequency

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